



T-29-21

SILICON SMALL-SIGNAL TRANSISTORS

PNP small-signal transistors, each in a plastic TO-92 envelope.

They are intended for use in audio amplifier driver stages and other general purpose applications.

NPN complementary types are 2PC1815 and 2PC1815L.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CB0}$	max.	50 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	50 V
Collector current (DC)	$-I_C$	max.	150 mA
Total power dissipation at $T_{amb} \leq 25^\circ C$	P_{tot}	max.	500 mW
Collector-emitter saturation voltage $-I_C = 100 \text{ mA}; -I_B = 10 \text{ mA}$	$-V_{CEsat}$	max.	0.3 V
DC current gain $-I_C = 2 \text{ mA}; -V_{CE} = 6 \text{ V}$	h_{FE}	min.	120
		max.	700

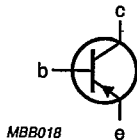
MECHANICAL DATA

Dimensions in mm

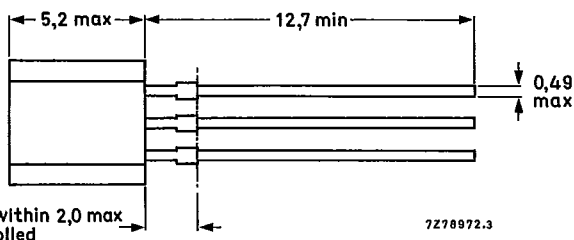
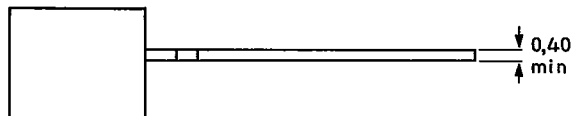
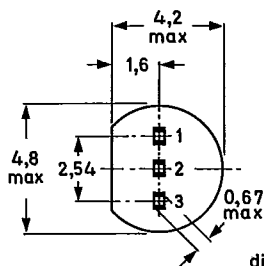
Fig.1 TO-92

Pinning

- 1 = base
- 2 = collector
- 3 = emitter



MBB01B



diameter within 2,0 max is uncontrolled

7278972.3

2PA1015
2PA1015L

PHILIPS INTERNATIONAL
查询 2PA1015L 供应商

56E D ■ 7110826 0042699 021 ■ PHIN

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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	-V _{CB0}	max.	50 V
Collector-emitter voltage (open base)	-V _{CEO}	max.	50 V
Emitter-base voltage (open collector)	-V _{EBO}	max.	5.0 V
Collector current (DC)	-I _C	max.	150 mA
Base current (DC)	-I _B	max.	50 mA
Total power dissipation at T _{amb} ≤ 25 °C	P _{tot}	max.	500 mW
Junction temperature	T _j	max.	150 °C
Storage temperature range	T _{stg}		-65 to + 150 °C

THERMAL RESISTANCE

From junction to ambient in free air	R _{th j-a}	=	250 K/W
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CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current -I _E = 0; -V _{CB} = 50 V	-I _{CB0}	max.	100 nA
Emitter cut-off current -I _C = 0; -V _{EB} = 5 V	-I _{EBO}	max.	100 nA
DC current gain -I _C = 150 mA; -V _{CE} = 6 V -I _C = 2 mA; -V _{CE} = 6 V *	h _{FE}	min.	25
	h _{FE}	min.	120
	h _{FE}	max.	700
Collector-emitter saturation voltage -I _C = 100 mA; -I _B = 10 mA	-V _{CEsat}	max.	0.3 V
Base-emitter saturation voltage -I _C = 100 mA; -I _B = 10 mA	-V _{BEsat}	max.	1.1 V
Transition frequency -I _C = 1 mA; -V _{CE} = 10 V	f _T	min.	80 MHz
Collector-output capacitance -I _E = 0; -V _{CB} = 10 V; f = 1 MHz	C _{ob}	typ.	4 pF
		max.	7 pF
Noise figure -I _C = 100 μA; -V _{CE} = 6 V; R _s = 10 kΩ; f = 1 kHz	2PA1015 2PA1015L	F	max. 10 dB
		F	max. 6 dB

* Classification of h_{FE}

Group	Y	GR	BL
Range	120 - 240	200 - 400	350 - 700